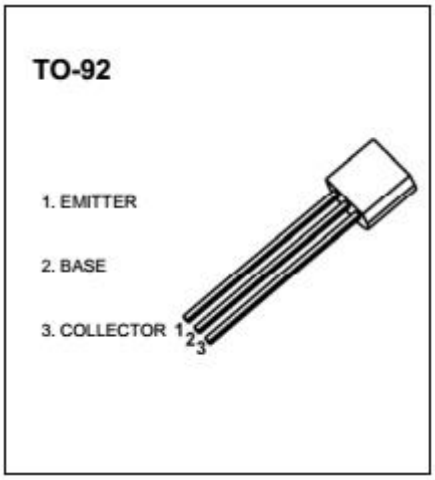
isc Silicon PNP Power Transistor MPSA92G



DESCRIPTION

- Low Saturation Voltage-
  : $V_{CE(sat)}$= 0.5V(Max)@ I_C =20mA

APPLICATIONS

- Designed for high voltage control circuit applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	0.5	A
P_C	Collector Power Dissipation @T_C=25℃	1.5	W
T_J	Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=100μA, I_E=0	300		V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=1mA , I_B=0	300		V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E= 100μA, I_C=0	5		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=20mA; I_B= 2mA		0.5	V
$V_{BE(sat)}$	base-emitter saturation voltage	I_C= 20mA; I_B=2mA		0.9	V
I_{CBO}	collector cut-off current	V_{CB} =200V,I_E = 0		0.25	uA
I_{EBO}	Emitter Cutoff Current	V_{EB}=3V; I_C=0		0.1	uA
h_{FE-1}	DC Current Gain	I_C= 30mA ; V_{CE}= 10V	25		